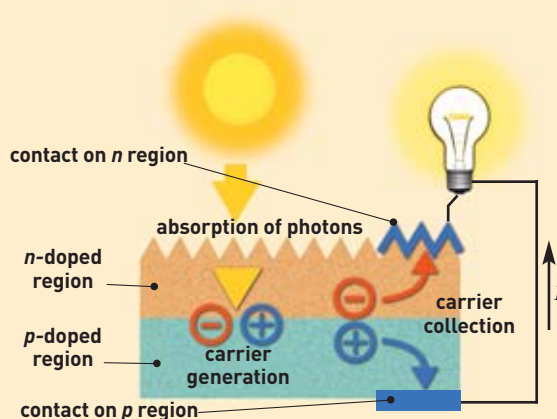


D How does a photovoltaic solar cell work?

The **photovoltaic effect** used in **solar cells** allows direct conversion of light energy from the Sun's rays into electricity, by way of the generation, and transport inside a **semiconductor** material, of positive and negative electric charges, through the action of light. This material features two regions, one exhibiting an excess of **electrons**, the other an electron deficit, respectively referred to as ***n*-type doped**, and ***p*-type doped**. When the former is brought into contact with the latter, excess electrons from the *n* material diffuse into the *p* material. The initially *n*-doped region becomes positively charged, and the initially *p*-doped region negatively charged. An electric field is thus set up between them, tending to force electrons back into the *n* region, and holes back into the *p* region. A **junction** (so-called *p*-*n* junction) has been set up. By placing metallic contacts on the *n* and *p* regions, a **diode** is obtained. When the junction is illuminated, **photons** having an energy equal to, or higher than, the width of the forbidden band, or **band gap**, yield their energy to the atoms, each photon causing an electron to move from the **valence band** to the **conduction band**, leaving behind it in turn a hole, also able to move around the material, thus



giving rise to an **electron-hole pair**. Should a load be positioned at the cell's terminals, electrons from the *n* region will migrate back to the holes in the *p* region, by way of the outside connection, giving rise to a potential difference: an electric current passes (see Figure).

The effect thus involves, basically, the material's semiconducting properties, and its doping, to improve **conductivity**. **Silicon**, now used in most cells, was selected for the presence of four **valence** electrons in its outermost shell (column IV of the Mendeleyev periodic table). In solid silicon, each atom - termed a tetravalent atom - is bound to four neighbors, and all electrons in the outermost shell participate in the bonds. Should a silicon atom be substituted for by an atom from column V

(a phosphorus atom, for instance), one of its five valence electrons is not involved in the bonds; as a result of thermal agitation, it soon moves to the conduction band, thus becoming free to move through the crystal, leaving behind it an immobile hole, bound to the doping atom. There is electron conduction, and the semiconductor is designated as an ***n*-type doped semiconductor**. If, on the other hand, a silicon atom is substituted for by an atom from column III (boron, for instance), carrying three valence electrons, one electron is missing, if all bonds are to be maintained, and an electron may quickly move in to fill this gap, taking up the vacant orbital, as a result of thermal agitation. A hole thus arises in the valence band, contributing to conduction, and the semiconductor is said to be a ***p*-type doped semiconductor**. Atoms of elements such as boron or phosphorus are thus doping agents in silicon. Photovoltaic cells are assembled into **modules**.

Note: In *Organic photovoltaic cells: towards an all-polymer path...*, you will find the operating principle of organic photovoltaic cells ([Box, p. 122](#)).

Operating principle of an organic photovoltaic cell

Following absorption of **photons** by the **polymer**, bound **electron-hole pairs** (excitons) are generated, subsequently undergoing dissociation. Owing to inherent limitations in organic materials (exciton lifetime, low charge mobility), only a small fraction of photon-generated electron-hole pairs effectively contribute to the photocurrent. One of the main ideas is to achieve volume distribution of the photogeneration sites, to enhance exciton dissociation. This approach is based on increasing **junction** surface area, through deployment of an interpenetrating network of the donor-acceptor (D-A) type, effecting transport of holes (P^+) to the **anode** (indium-tin oxide [ITO]), and of electrons (e^-) to the metallic **cathode** (made e.g. of aluminum [Al]). While quantum separation efficiency, for photoinduced charges in systems associating a **semiconducting** polymer (of PPV or polythiophene type) with a fullerene derivative (PCBM), is thus close to unity, the challenge now is to restrict recombination and trapping processes limiting charge transport and collection at the electrodes, to improve overall device efficiency, this currently still being low (less than 5%). The rise of the pathway is also heavily dependent on mastery and understanding of cell aging mechanisms, but equally on mastery of thin-film technologies, to achieve protection of the device against atmospheric oxygen and water vapor.

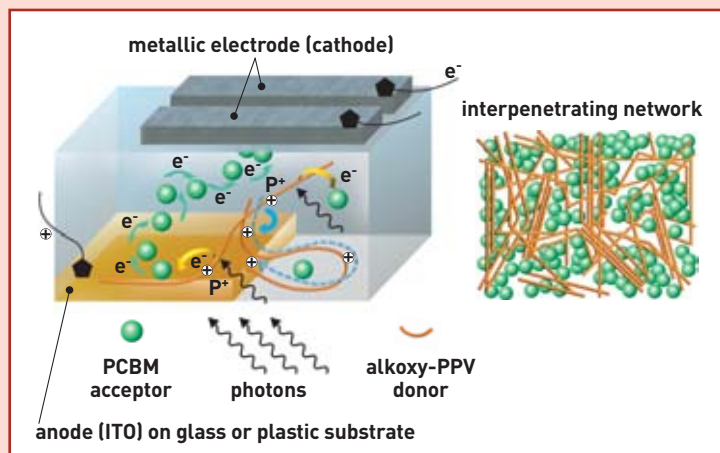


Figure from a presentation by S. Sariciffici (www.itiis.at)

The blue dotted line shows the trajectory of holes inside the material.